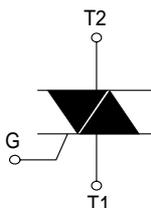
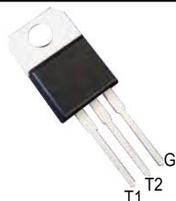
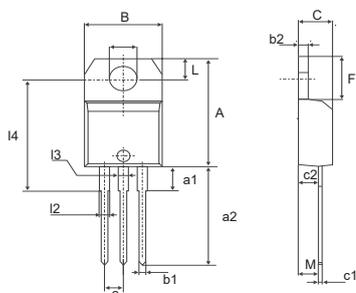


BTB/BTA24

Discrete Triacs(Non-Isolated/Isolated)



Dimensions TO-220AB



REF.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
Øl	3.75		3.85	0.147		0.151
H	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
l2	1.14		1.70	0.044		0.066
l3	1.14		1.70	0.044		0.066
M		2.60			0.102	

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit	
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-220AB	$T_c=100^\circ\text{C}$	24	A	
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial = 25°C)	F=60Hz	$t=16.7\text{ms}$	260	A	
		F=50Hz	$t=20\text{ms}$	250		
I_t^2	I_t^2 Value for fusing	$t_p = 10\text{ms}$		340	A^2s	
di/dt	Critical rate of rise of on-state current $I_G=2 \times I_{GT}$, $t_r \leq 100\text{ns}$	F=120Hz	$T_j=125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$	
V_{DSM}/V_{RSM}	Non repetitive surge peak off-state voltage	$t_p=10\text{ms}$	$T_j=25^\circ\text{C}$	$V_{DRM}/V_{RRM} + 100$	V	
I_{GM}	Peak gate current	$t_p=20\mu\text{s}$	$T_j=125^\circ\text{C}$	4	A	
$P_{G(AV)}$	Average gate power dissipation	$T_j=125^\circ\text{C}$		1	W	
T_{stg} T_j	Storage junction temperature range Operating junction temperature range				- 40 to+150 - 40 to+125	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$, unless otherwise specified)

■ SNUBBERLESS™ and LOGIC LEVEL(3 Quadrants)

Symbol	Test Conditions	Quadrant		BTB/BTA		Unit
				CW	BW	
$I_{GT}(1)$	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	35	50	mA
V_{GT}		I - II - III	MAX.	1.3		V
V_{GD}	$V_D=V_{DRM}$ $R_L=3.3\text{k}\Omega$ $T_j=125^\circ\text{C}$	I - II - III	MIN.	0.2		V
$I_H(2)$	$I_T=500\text{mA}$		MAX.	50	75	mA
I_L	$I_G=1.2 I_{GT}$	I - III	MAX.	70	80	mA
		II		80	100	
$dV/dt(2)$	$V_D=67\% V_{DRM}$ gate open $T_j=125^\circ\text{C}$		MIN.	500	1000	$\text{V}/\mu\text{s}$
$(di/dt)_c(2)$	Without snubber $T_j=125^\circ\text{C}$		MIN.	13	22	A/ms



BTB/BTA24

Discrete Triacs(Non-Isolated/Isolated)

■ STANDARD (4 Quadrants)

Symbol	Test Conditions	Quadrant		Value	Unit
I_{GT} (1)	$V_D=12V R_L=33\Omega$	I - II - III IV	MAX.	50 100	mA
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} R_L=3.3\Omega T_j = 125^\circ C$	ALL	MIN.	0.2	V
I_H (2)	$I_T=500mA$		MAX.	80	mA
I_L	$I_G=1.2 I_{GT}$	I - III - IV	MAX.	70	mA
		II		160	
dV/dt (2)	$V_D= 67\% V_{DRM}$ gate open $T_j=125^\circ C$		MIN.	500	V/ μs
$(dV/dt)_c$ (2)	$(dI/dt)_c =13.3A/ms T_j =125^\circ C$		MIN.	10	V/ μs

STATIC CHARACTERISTICS

Symbol	Test Conditions			Value	Unit
V_{TM} (2)	$I_{TM}=35A t_p=380\mu s$	$T_j = 25^\circ C$	MAX.	1.55	V
V_{to} (2)	Threshold voltage	$T_j = 125^\circ C$	MAX.	0.85	V
R_d (2)	Dynamic resistance	$T_j = 125^\circ C$	MAX.	16	m Ω
I_{DRM}	$V_{DRM} = V_{RRM}$	$T_j = 25^\circ C$	MAX.	5	μA
I_{RRM}		$T_j = 125^\circ C$		3	mA

Note 1: minimum IGT is guaranteed at 5% of IGT max.

Note 2: for both polarities of A2 referenced to A1

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	0.8	$^\circ C/W$
$R_{th(j-a)}$	Junction to ambient	60	$^\circ C/W$

PRODUCT SELECTOR

Part Number	Voltage (xxx)		Sensitivity	Type	Package
	200 V	~ 1000 V			
BTBV/BTA24	X	X	50 mA	Standard	TO-220AB

OTHER INFORMATION

Part Number	Marking	Weight	Base quantity	Packing mode
BTB/BTA24	BTB/BTA24	2 g	250	Bulk



BTB/BTA24

Discrete Triacs(Non-Isolated/Isolated)

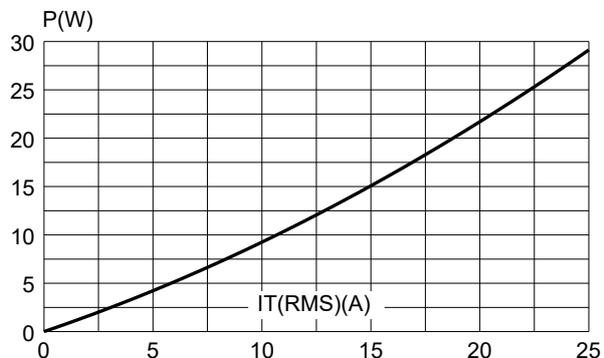


Fig.1: Maximum power dissipation versus RMS on-state current(full cycle).

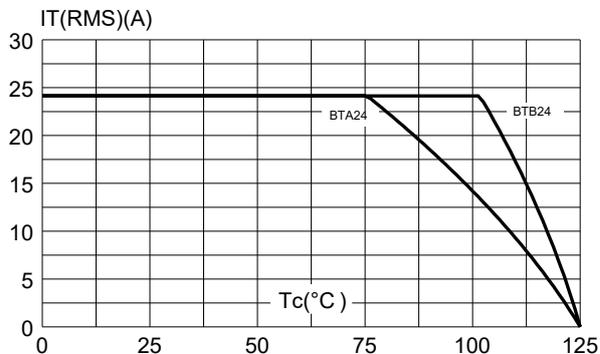


Fig.2-1: RMS on-state current versus case temperature (full cycle).

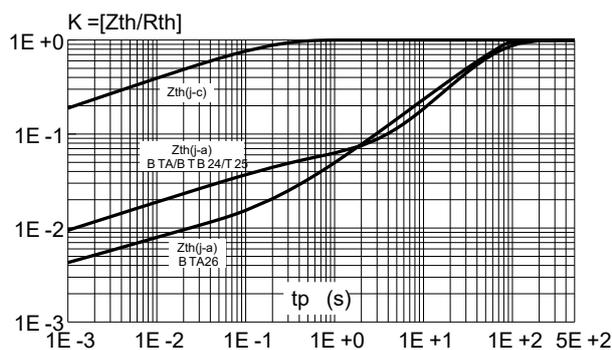


Fig.3:Relative variation of thermal impedance versus pulse duration.

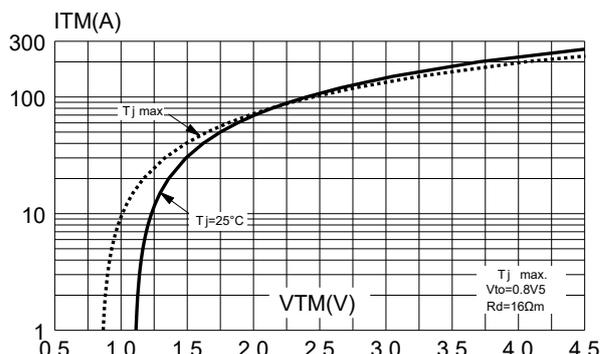


Fig.4:On-state characteristics(maximum values).

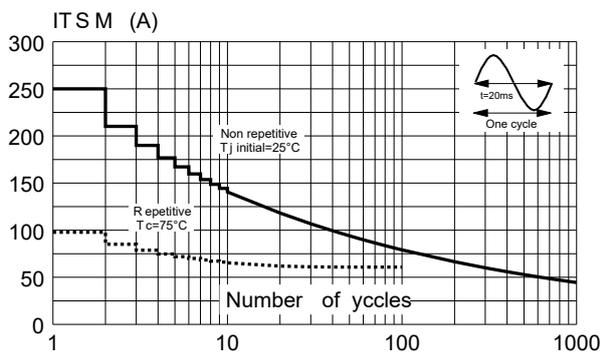


Fig.5: Surge peak on-state current versus number of cycles.

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Discrete Triacs(Non-Isolated/Isolated)

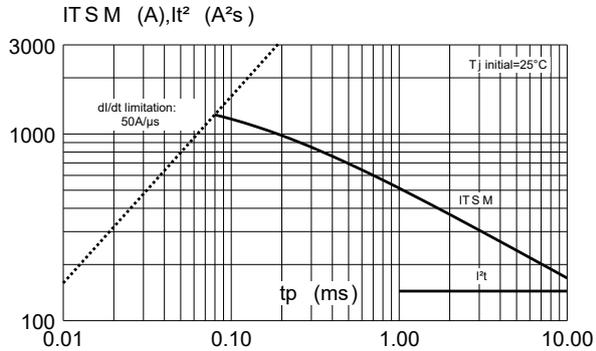


Fig.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$, and corresponding value of I_t^2 .

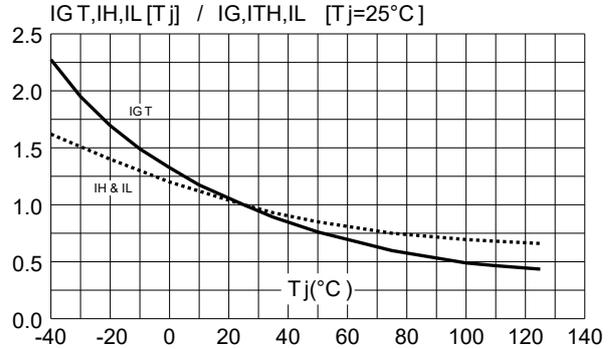


Fig.7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

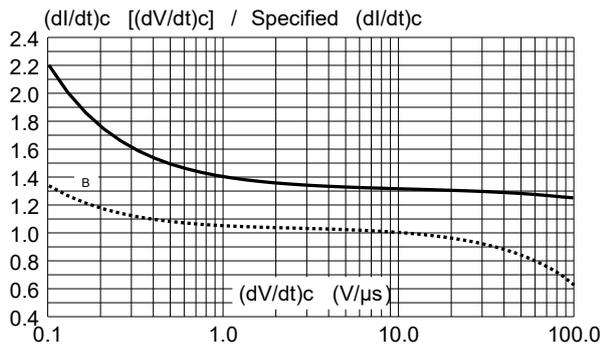


Fig.8: Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$ (typical values).

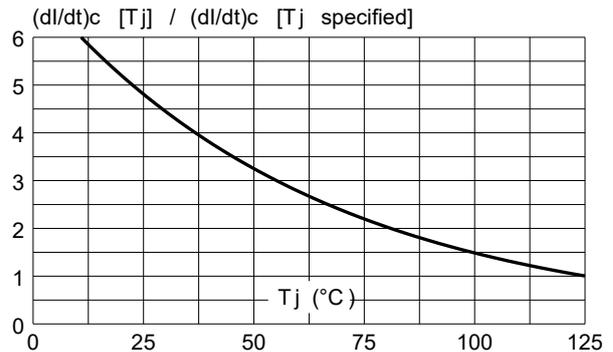


Fig.9: Relative variation of critical rate of decrease of main current versus junction temperature.